

/ Descriptions

KF \$0) GE G Silicon PNP transistor in a TO-92 Plastic Package.

/ Features

Low noise, high DC current gain, high breakdown voltage.

/ Applications

Low noise audio amplifier applications.

/ Equivalent Circuit



/ Pinning



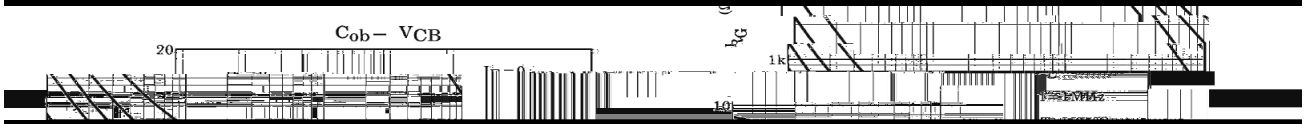
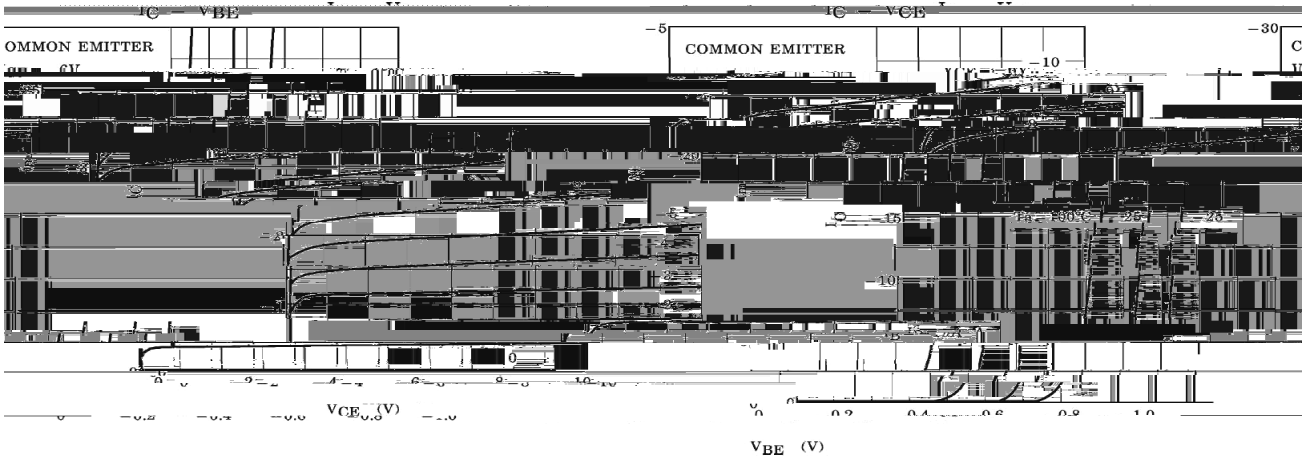
PIN1 Base PIN 2 Collector PIN 3 Emitter

/ hFE Classifications & Marking

h _{FE} Classifications Symbol	GR	BL
h _{FE} Range	200~400	350~700

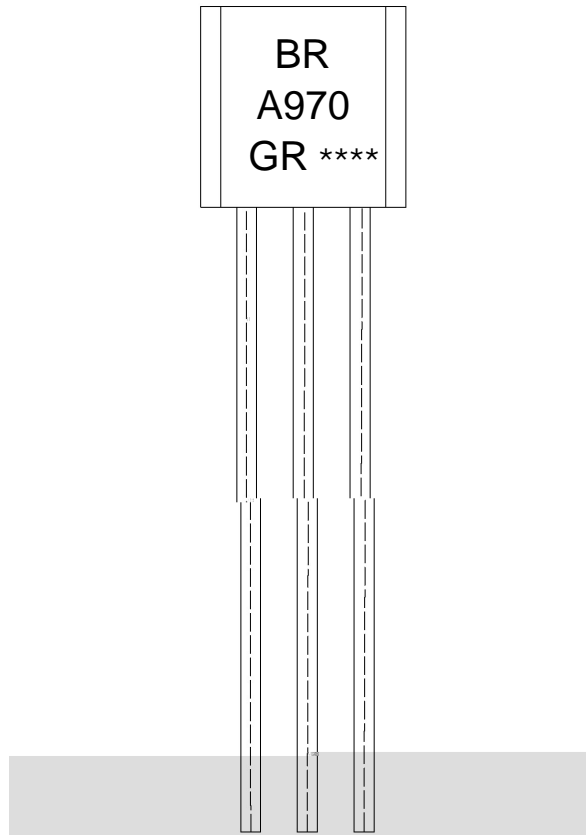
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	-120	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Emitter Current – Continuous	I_E	100	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	152 591iw560.J/TT7 161 Tf28 TD0107	

/ Electrical Characteristic Curve



2SA970
Rev.E Mar.-2016

/ Marking Instructions



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80.
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Note:

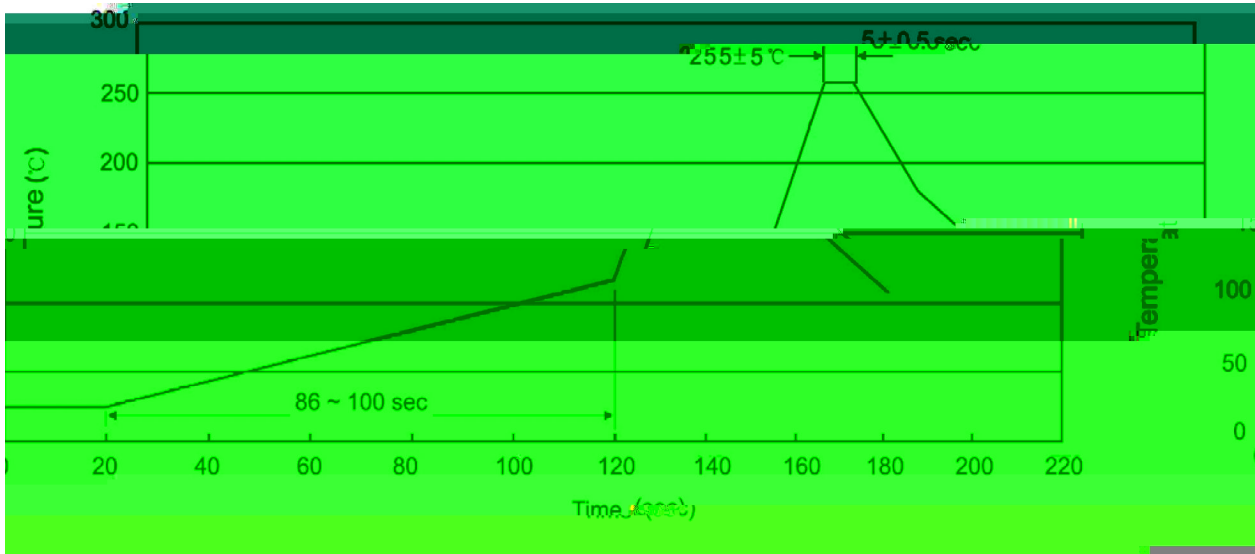
BR: Company Code.

A970: Product Type Code.

GR: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|--------|-----|-----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 | | 5.. | 0.5sec; | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270..5 10...1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

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